

# FX20ASJ-03F

High-Speed Switching Use Pch Power MOS FET

REJ03G0248-0200 Rev.2.00 Dec 19, 2008

### **Features**

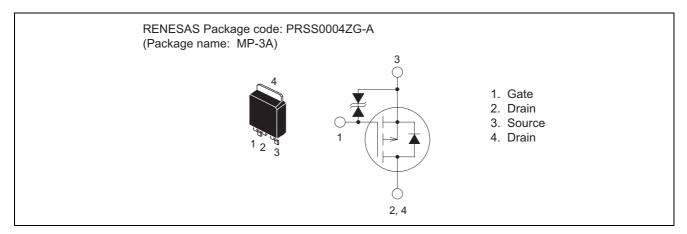
• Drive voltage: 4 V

 $\bullet \quad V_{DSS}:-30~V$ 

•  $r_{DS(ON) (max)}$ : 0.12  $\Omega$ 

•  $I_D: -20 A$ 

### **Outline**



# **Applications**

Motor control, lamp control, solenoid control, DC-DC converters, etc.

## **Maximum Ratings**

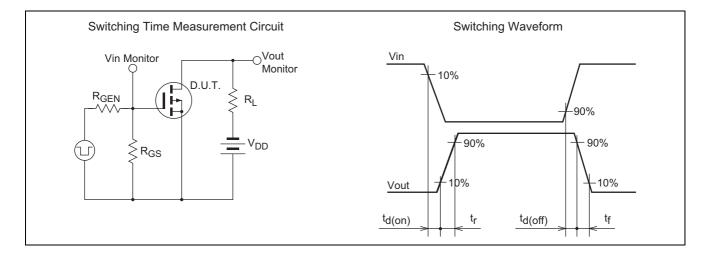
 $(Tc = 25^{\circ}C)$ 

Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V <sub>DSS</sub>	-30	V	V <sub>GS</sub> = 0 V
Gate-source voltage	V <sub>GSS</sub>	±20	V	$V_{DS} = 0 V$
Drain current	I <sub>D</sub>	-20	Α	
Drain current (Pulsed)	I <sub>DM</sub>	- 40	Α	
Avalanche current (Pulsed)	I <sub>DA</sub>	-5	Α	L = 10 μH
Source current	Is	-20	Α	
Source current (Pulsed)	I <sub>SM</sub>	- 40	Α	
Maximum power dissipation	P <sub>D</sub>	25	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

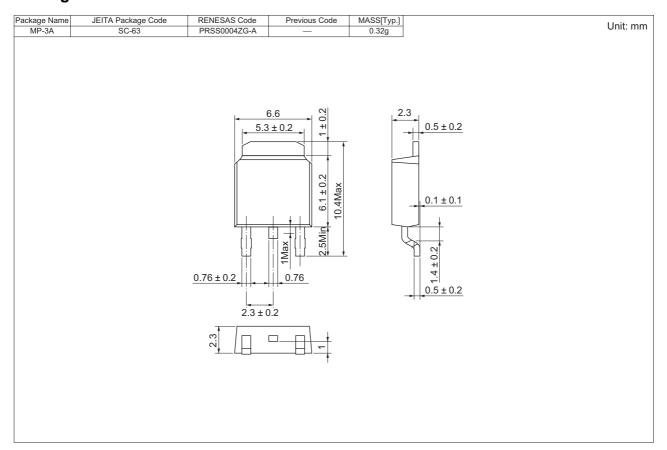
# **Electrical Characteristics**

 $(Tch = 25^{\circ}C)$ 

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-30	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	$V_{(BR)GSS}$	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0 \ V$
Drain-source leakage current	I <sub>DSS</sub>	_	_	100	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	$V_{GS(th)}$	-1.5	-2.0	-2.5	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.085	0.12	Ω	$I_D = -10 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.145	0.20	Ω	$I_D = -2 A$ , $V_{GS} = -4 V$
Drain-source on-state voltage	V <sub>DS(ON)</sub>	_	-0.85	-1.2	V	$I_D = -10 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y <sub>fs</sub>	_	8	_	S	$I_D = -10 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss	_	500	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	100	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	80	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	6	_	ns	$V_{DD} = -15 \text{ V}, I_D = -10 \text{ A},$
Rise time	t <sub>r</sub>	_	8	_	ns	$V_{GS} = -10 \text{ V},$
Turn-off delay time	t <sub>d(off)</sub>	_	40	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t <sub>f</sub>	_	15	_	ns	
Source-drain voltage	V <sub>SD</sub>	_	-1.0	-1.5	V	I <sub>S</sub> = -10 A, V <sub>GS</sub> = 0 V
Thermal resistance	Rth(ch-c)	_	_	5.0	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	_	30	_	ns	$I_S = -10 \text{ A}, \text{ dis/dt} = -50 \text{ A/}\mu\text{s}$



# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX20ASJ-03F-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX20ASJ-03F

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application critical expensions of the purpose of any other military use. When exporting the products or technology described in this document for the purpose of military applications, and procedures required by such laws and regulations, and procedures required to the date this document in the such and the procedure of the procedure o



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

#### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510